MC10H145

16 x 4 Bit Register File (RAM)

The MC10H145 is a 16 x 4 bit register file. The active-low chip select allows easy expansion.

The operating mode of the register file is controlled by the $\overline{WE}$ input. When $\overline{WE}$ is "low" the device is in the write mode, the outputs are "low" and the data present at D_n input is stored at the selected address, when $\overline{WE}$ is "high," the device is in the read mode – the data state at the selected location is present at the Q_n outputs.

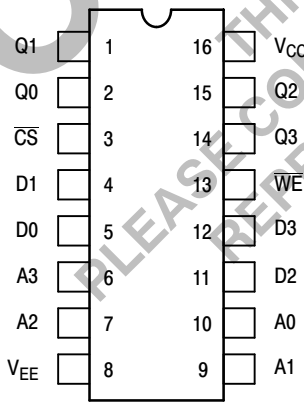
- Address Access Time, 4.5 ns Typical
- Power Dissipation, 700 mW Typical
- Improved Noise Margin 150 mV (Over Operating Voltage and Temperature Range)
- Voltage Compensated
- MECL 10K-Compatible

TRUTH TABLE

MODE	INPUT			OUTPUT
	$\overline{CS}$	$\overline{WE}$	D_n	Q_n
Write "0"	L	L	L	L
Write "1"	L	L	H	L
Read	L	H	X	Q
Disabled	H	X	X	L

Q-State of Addressed Cell

DIP PIN ASSIGNMENT

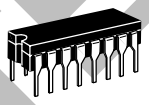


Pin assignment is for Dual–in–Line Package.
For PLCC pin assignment, see the Pin Conversion Tables on page 6–11 of the Motorola MECL Data Book (DL122/D).

ON Semiconductor®

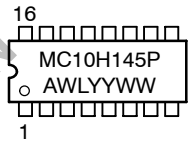
http://onsemi.com

MARKING DIAGRAMS

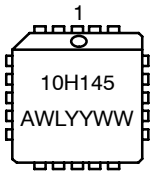


CDIP–16
L SUFFIX
CASE 620

PDIP–16
P SUFFIX
CASE 648



PLCC–20
FN SUFFIX
CASE 775

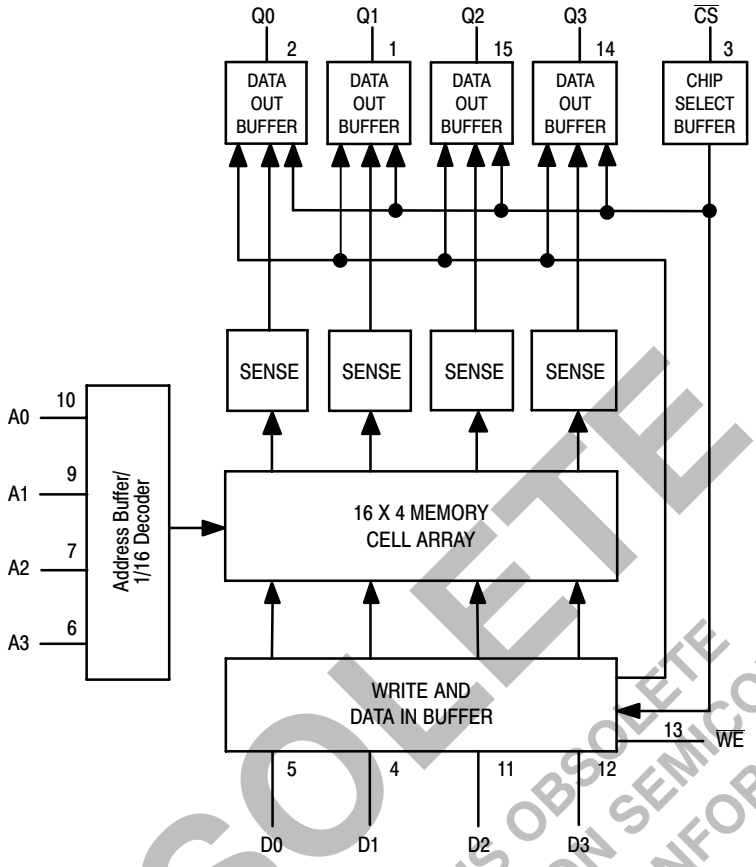


A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC10H145L	CDIP–16	25 Units/Rail
MC10H145P	PDIP–16	25 Units/Rail
MC10H145FN	PLCC–20	xx Units/Rail

BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Characteristic	Rating	Unit
V_{EE}	Power Supply (V_{CC} = 0)	−8.0 to 0	Vdc
V_I	Input Voltage (V_{CC} = 0)	0 to V_{EE}	Vdc
I_{out}	Output Current − Continuous − Surge	50 100	mA
T_A	Operating Temperature Range	0 to +75	°C
T_{stg}	Storage Temperature Range − Plastic − Ceramic	−55 to +150 −55 to +165	°C

ELECTRICAL CHARACTERISTICS (V_{EE} = −5.2 V ±5%) (See Note)

Symbol	Characteristic	0°		25°		75°		Unit
		Min	Max	Min	Max	Min	Max	
I_E	Power Supply Current	−	160	−	163	−	165	mA
I_{inH}	Input Current High	−	375	−	220	−	220	μA
I_{inL}	Input Current Low	0.5	−	0.5	−	0.3	−	μA
V_{OH}	High Output Voltage	−1.02	−0.84	−0.98	−0.81	−0.92	−0.735	Vdc
V_{OL}	Low Output Voltage	−1.95	−1.63	−1.95	−1.63	−1.95	−1.60	Vdc
V_{IH}	High Input Voltage	−1.17	−0.84	−1.13	−0.81	−1.07	−0.735	Vdc
V_{IL}	Low Input Voltage	−1.95	−1.48	−1.95	−1.48	−1.95	−1.45	Vdc

1. Each MECL 10H series circuit has been designed to meet the dc specifications shown in the test table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 lfpm is maintained. Outputs are terminated through a 50-ohm resistor to −2.0 volts.

AC PARAMETERS

Symbol	Characteristics	MC10H145 T_A = 0 to +75°C, V_{EE} = −5.2 Vdc ±5% Min	Max	Unit	Conditions
	Read Mode			ns	Measured from 50% of input to 50% of output. See Note 2.
t_{ACS}	Chip Select Access Time	0	4.0		
t_{RCS}	Chip Select Recovery Time	0	4.0		
t_{AA}	Address Access Time	0	6.0		
	Write Mode			ns	t_{WSA} = 3.5 ns
t_W	Write Pulse Width	6.0	–		Measured at 50% of input to 50% of output. t_W = 6.0 ns.
t_{WSD}	Data Setup Time Prior to Write	0	–		
t_{WHD}	Data Hold Time After Write	1.5	–		
t_{WSA}	Address Setup Time Prior to Write	3.5	–		
t_{WHA}	Address Hold Time After Write	1.5	–		
t_{WSCS}	Chip Select Setup Time Prior to Write	0	–		
t_{WHCS}	Chip Select Hold Time After Write	1.5	–		
t_{WS}	Write Disable Time	1.0	4.0		
t_{WR}	Write Recovery Time	1.0	4.0		
	Chip Enable Strobe Mode			ns	Guaranteed but not tested on standard product. See Figure 1.
t_{CSD}	Data Setup Prior to Chip Select	0	–		
t_{CSW}	Write Enable Setup Prior to Chip Select	0	–		
t_{CSA}	Address Setup Prior to Chip Select	0	–		
t_{CHD}	Data Hold Time After Chip Select	1.0	–		
t_{CHW}	Write Enable Hold Time After Chip Select	0	–		
t_{CHA}	Address Hold Time After Chip Select	2.0	–		
t_{CS}	Chip Select Minimum Pulse Width	4.0	–		
t_r, t_f	Rise and Fall Time			ns	Measured between 20% and 80% points.
	Address to Output	0.6	2.5		
	CS to Output	0.6	2.5		
	Capacitance			pF	Measured with a pulse technique.
C_{in}	Input Capacitance	–	6.0		
C_{out}	Output Capacitance	–	8.0		

NOTES:
1. Test circuit characteristics: R_T = 50 Ω, MC10H145. $C_L \leq$ 5.0 pF (including jig and Stray Capacitance). Delay should be derated 30 ps/pF for capacitive loads up to 50 pF.
2. The maximum Address Access Time is guaranteed to be the worst-case bit in the memory.
3. For proper use of MECL in a system environment, consult MECL System Design Handbook.

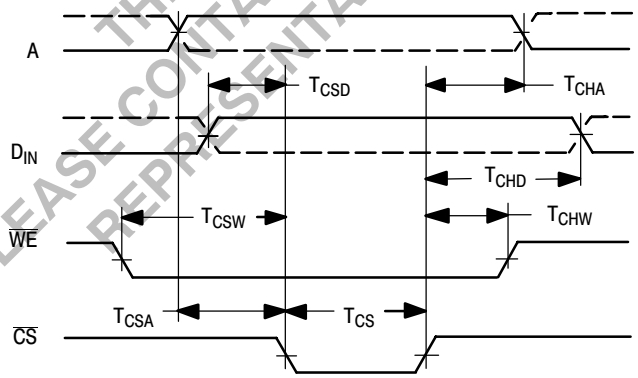
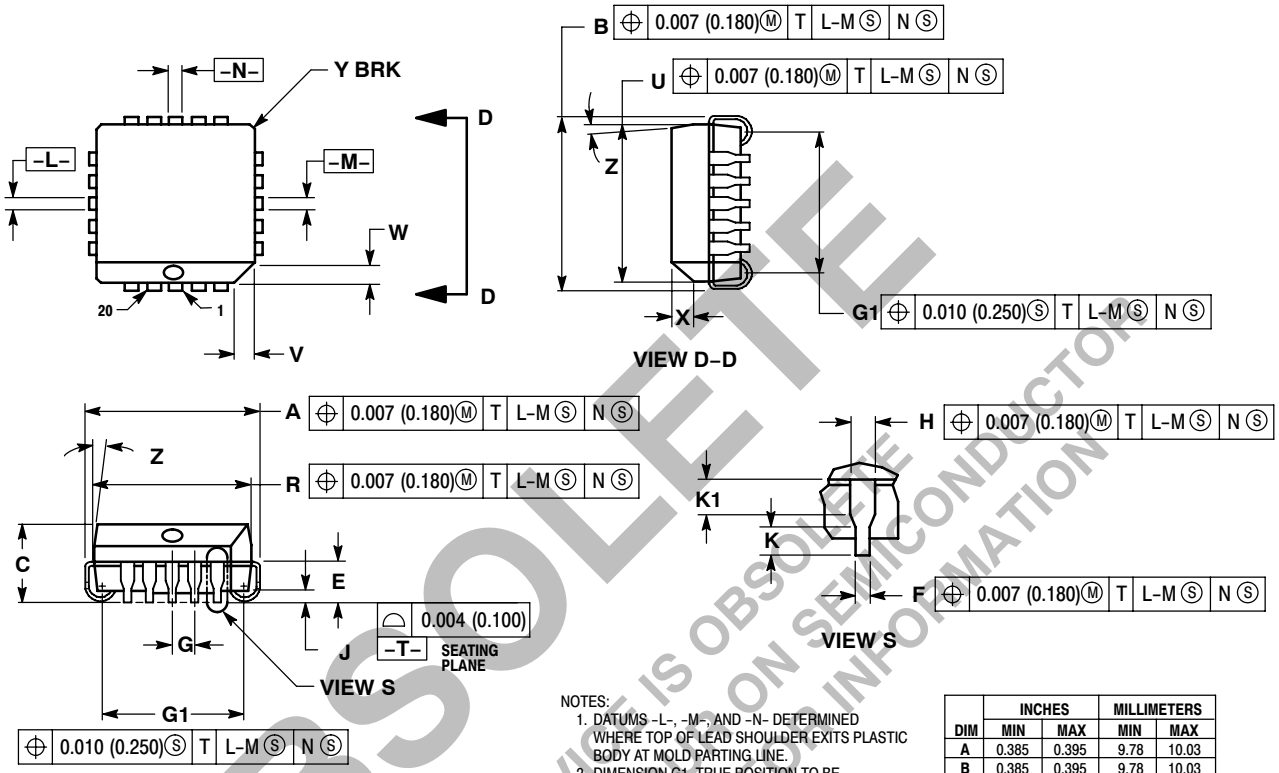


Figure 1. Chip Enable Strobe Mode

PACKAGE DIMENSIONS

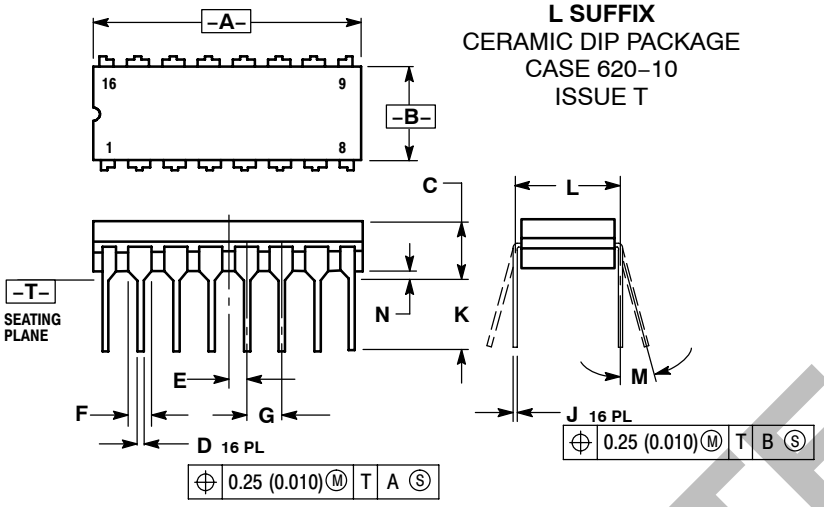
PLCC–20
FN SUFFIX
PLASTIC PLCC PACKAGE
CASE 775–02
ISSUE C



NOTES:
1. DATUMS –L–, –M–, AND –N– DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.
2. DIMENSION G1, TRUE POSITION TO BE MEASURED AT DATUM –T–, SEATING PLANE.
3. DIMENSIONS R AND U DO NOT INCLUDE MOLD FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
5. CONTROLLING DIMENSION: INCH.
6. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300). DIMENSIONS R AND U ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
7. DIMENSION H DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.385	0.395	9.78	10.03
B	0.385	0.395	9.78	10.03
C	0.165	0.180	4.20	4.57
E	0.090	0.110	2.29	2.79
F	0.013	0.019	0.33	0.48
G	0.050 BSC		1.27 BSC	
H	0.026	0.032	0.66	0.81
J	0.020	---	0.51	---
K	0.025	---	0.64	---
R	0.350	0.356	8.89	9.04
U	0.350	0.356	8.89	9.04
V	0.042	0.048	1.07	1.21
W	0.042	0.048	1.07	1.21
X	0.042	0.056	1.07	1.42
Y	---	0.020	---	0.50
Z	2°	10°	2°	10°
G1	0.310	0.330	7.88	8.38
K1	0.040	---	1.02	---

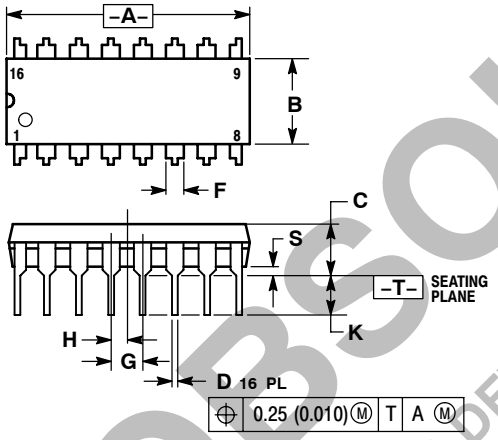
CDIP–16
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	---	0.200	---	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

PDIP–16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada
Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5773–3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

MC10H145/D